

Internally Matched Power GaAs FETs (C-Band)

Features

- High power
 - $P_{1dB} = 39$ dBm at 4.9 GHz to 5.1 GHz
- High gain
 - $G_{1dB} = 9.5$ dB at 4.9 GHz to 5.1 GHz
- Broad band internally matched
- Hermetically sealed package

RF Performance Specifications ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10V$ $f = 4.9 \sim 5.1$ GHz	dBm	38.0	39.0	–
Power Gain at 1dB Compression Point	G_{1dB}		dB	8.5	9.5	–
Drain Current	I_{DS}		A	–	2.2	2.8
Power Added Efficiency	η_{add}		%	–	32	–
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th}(c-c)$	$^\circ\text{C}$	–	–	80

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 3.0$ A	mS	–	1800	–
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3V$ $I_{DS} = 40$ mA	V	-2	-3.5	-5
Saturated Drain Current	I_{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	5.8	7.5
Gate to Source Breakdown Voltage	V_{GSO}	$I_{GS} = -120$ μA	V	-5	–	–
Thermal Resistance	$R_{th}(c-c)$	Channel to case	$^\circ\text{C/W}$	–	2.3	3.5

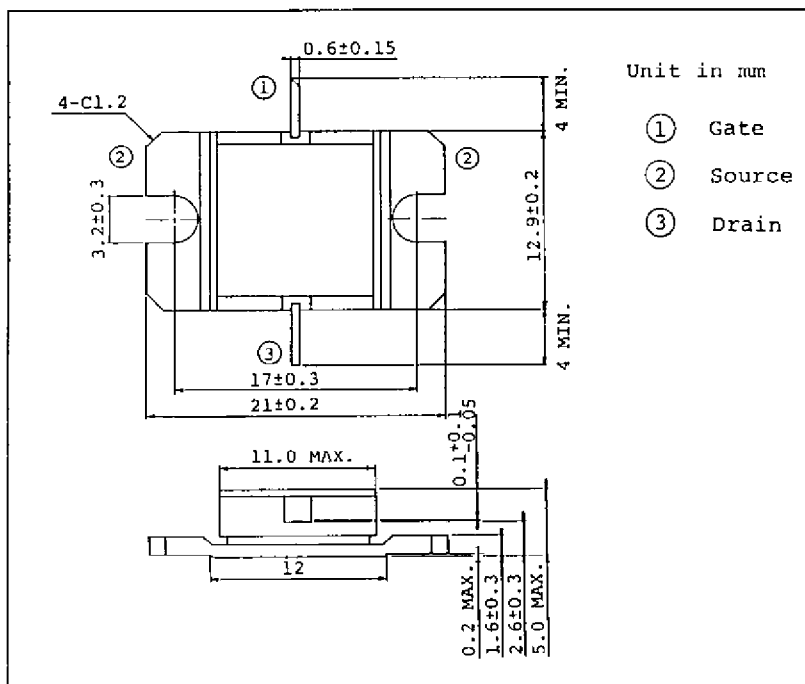
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Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Unit	Rating
Drain Source Voltage	V_{DS}	V	15
Gate Source Voltage	V_{GS}	V	-5
Drain Current	I_D	A	8
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_T	W	37.5
Channel Temperature	T_{ch}	$^\circ\text{C}$	175
Storage Temperature	T_{stg}	$^\circ\text{C}$	-65~175

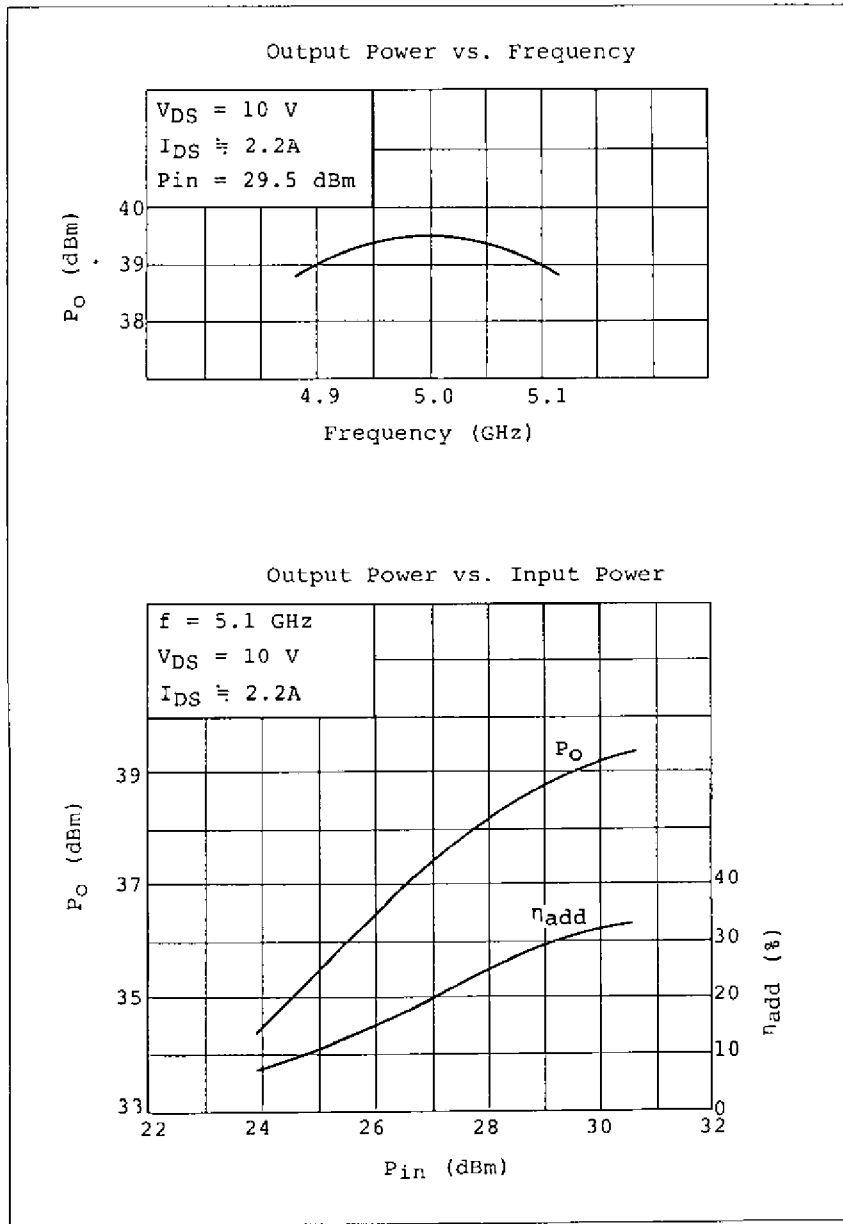
Package Outline (2-11D1B)



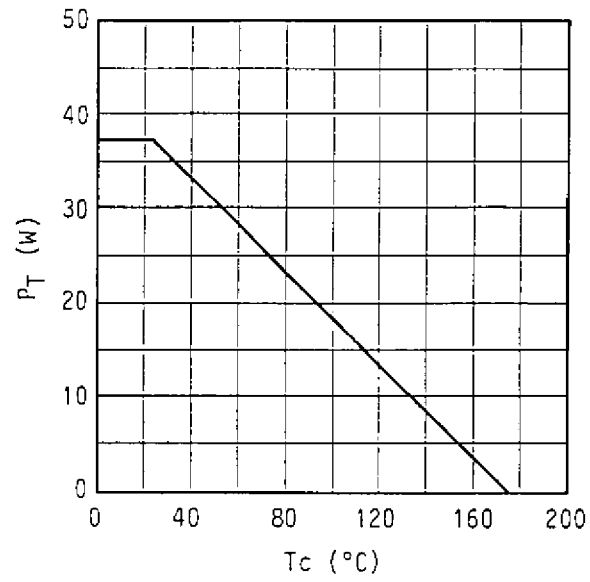
Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C .

RF Performances



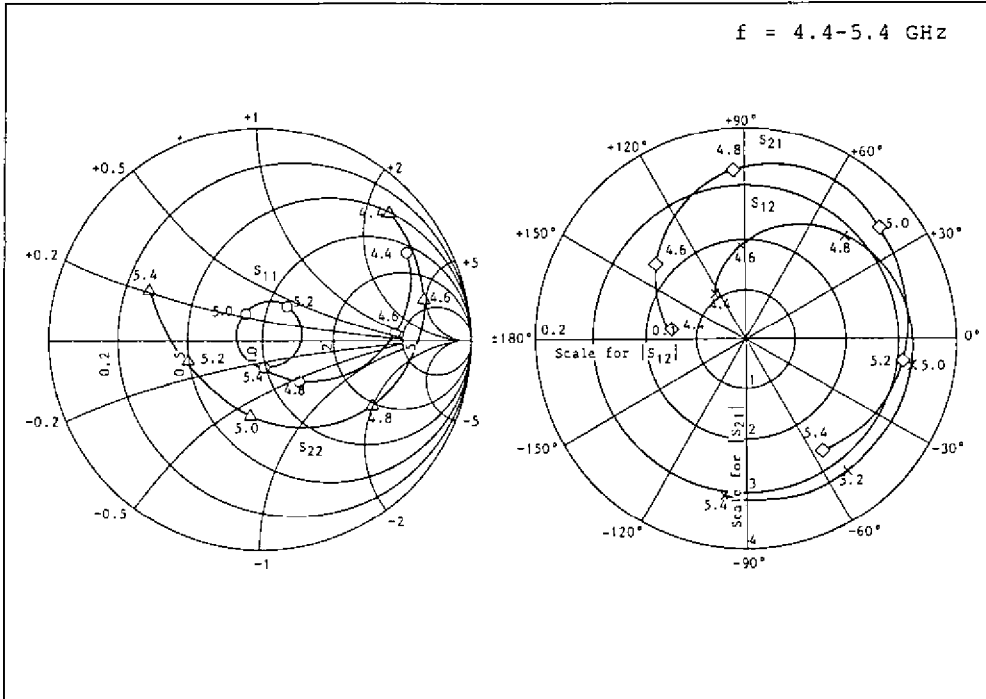
Power Dissipation vs. Case Temperature



**TIM4951-8 S-Parameters
(MAGN. and ANGLES)**

$V_{DS} = 10 \text{ V}, I_{DS} = 2.0 \text{ A}$

$f = 4.4\text{-}5.4 \text{ GHz}$



FREQUENCY (GHz)	S ₁₁		S ₁₂		S ₂₁		S ₂₂	
4.4	0.80	30	0.054	123	1.55	175	0.84	42
4.6	0.62	2	0.091	90	2.32	141	0.78	14
4.8	0.25	-46	0.146	44	3.32	96	0.60	-31
5.0	0.15	115	0.173	-6	3.54	39	0.34	-98
5.2	0.21	52	0.168	-52	3.19	-10	0.35	-162
5.4	0.15	-80	0.159	-95	2.78	-57	0.57	154